

TEMPERATURE DEPENDENCE OF GALVANOMAGNETIC PROPERTIES OF UNDOPED *n*-TYPE GaAs/GaAs AND *n*-TYPE InGaAs/InP LAYERS

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ABSTRACT

The magnetoresistance (MR) and the Hall-effect measurements in undoped *n*-type GaAs/GaAs and *n*-type In_{0.53}Ga_{0.47}As/InP samples in the temperature range 3.5 ÷ 300 K were carried out. We have obtained magnetoresistance data on the samples of *n*-type epilayers on SI GaAs and SI InP substrates made MBE technology. Magnetoresistance by measurements in constant magnetic fields vs. temperature are completed. The measurements reveal that the magnetoresistance of the samples strongly depends on the temperature and magnetic field.